

FDFMJ2P023Z

Integrated P-Channel PowerTrench® MOSFET and Schottky Diode –20V, –2.9A, 112mΩ

Features

MOSFET

- Max $r_{DS(on)}$ = 112mΩ at $V_{GS} = -4.5V$, $I_D = -2.9A$
- Max $r_{DS(on)}$ = 160mΩ at $V_{GS} = -2.5V$, $I_D = -2.4A$
- Max $r_{DS(on)}$ = 210mΩ at $V_{GS} = -1.8V$, $I_D = -2.1A$
- Max $r_{DS(on)}$ = 300mΩ at $V_{GS} = -1.5V$, $I_D = -1.0A$
- Low gate charge, high power and current handline capability
- HBM ESD protection level > 1.5KV typical (Note 3)

Schottky

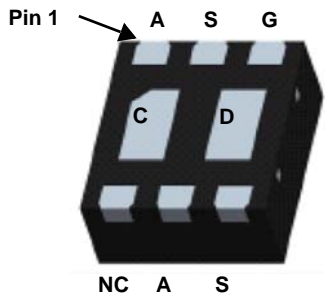
- $V_F < 400mV$ @ 100mA
- RoHS Compliant



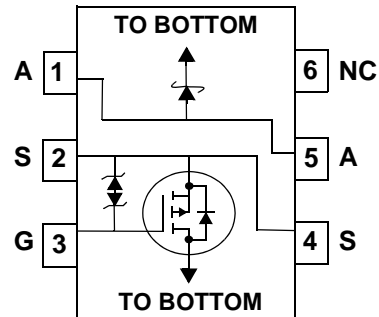
General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features a MOSFET with low on-state resistance and an independently connected low forward voltage schottky diode for minimum conduction losses.

The SC-75 MicroFET package offers exceptional thermal performance for it's physical size and is well suited to linear mode applications.



SC-75 MicroFET



MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Drain Current -Continuous	-2.9	A
	-Pulsed	-12	
P_D	Power Dissipation	1.4	W
	Power Dissipation	0.7	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C
V_{RRM}	Schottky Repetitive Peak Reverse Voltage	30	V
I_O	Schottky Average Forward Current	1	A

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	89	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	182	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.P23	FDFMJ2P023Z	SC-75 MicroFET	7"	8 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		-13		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.4	-0.7	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		2.3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -4.5\text{V}, I_D = -2.9\text{A}$		93	112	m Ω
		$V_{GS} = -2.5\text{V}, I_D = -2.4\text{A}$		128	160	
		$V_{GS} = -1.8\text{V}, I_D = -2.1\text{A}$		173	210	
		$V_{GS} = -1.5\text{V}, I_D = -1.0\text{A}$		217	300	
		$V_{GS} = -4.5\text{V}, I_D = -2.9\text{A}, T_J = 125^\circ\text{C}$		130	160	
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -2.9\text{A}$		7		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		300	400	pF
C_{oss}	Output Capacitance			55	75	pF
C_{rss}	Reverse Transfer Capacitance			45	70	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{V}, I_D = -2.9\text{A}, V_{GS} = -4.5\text{V}, R_{GEN} = 6\Omega$		5	10	ns
t_r	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			23	37	ns
t_f	Fall Time			12	22	ns
Q_g	Total Gate Charge	$V_{DD} = -5\text{V}, I_D = -2.9\text{A}, V_{GS} = -4.5\text{V}$		4.6	6.5	nC
Q_{gs}	Gate to Source Charge			0.6		nC
Q_{gd}	Gate to Drain "Miller" Charge			1.0		nC

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain-Source Diode Forward Current				-1.1	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -1.1\text{A}$		-0.9	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -2.9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		28	45	ns
Q_{rr}	Reverse Recovery Charge			15	27	nC

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

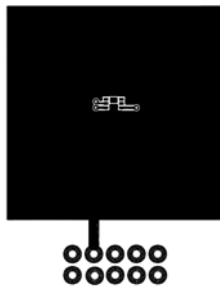
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Schottky Diode Characteristics

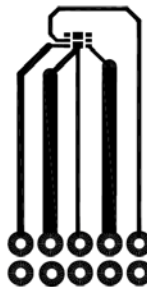
V_R	Reverse Voltage	$I_R = 100\text{mA}$	$T_J = 25^\circ\text{C}$	30		V
I_R	Reverse Leakage	$V_R = 10\text{V}$	$T_J = 25^\circ\text{C}$		0.39	2 μA
			$T_J = 85^\circ\text{C}$		0.04	0.2 mA
			$T_J = 125^\circ\text{C}$		0.4	2 mA
I_R	Reverse Leakage	$V_R = 20\text{V}$	$T_J = 25^\circ\text{C}$		0.86	4 μA
			$T_J = 85^\circ\text{C}$		0.06	0.3 mA
			$T_J = 125^\circ\text{C}$		0.62	3 mA
V_F	Forward Voltage	$I_F = 100\text{mA}$	$T_J = 25^\circ\text{C}$		380	400 mV
			$T_J = 85^\circ\text{C}$		300	350 mV
			$T_J = 125^\circ\text{C}$		250	300 mV
V_F	Forward Voltage	$I_F = 1\text{A}$	$T_J = 25^\circ\text{C}$		570	615 mV
			$T_J = 85^\circ\text{C}$		540	590 mV
			$T_J = 125^\circ\text{C}$		530	580 mV

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 89°C/W when mounted on a 1 in² pad of 2 oz copper



b. 182°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

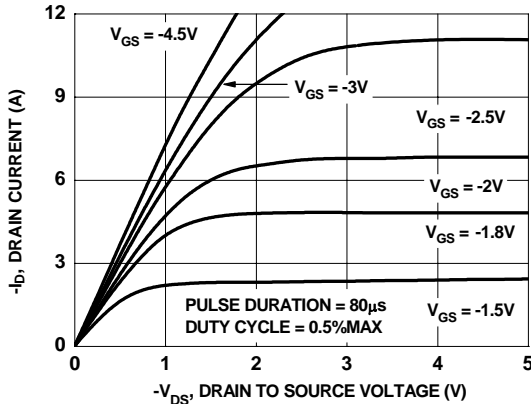


Figure 1. On-Region Characteristics

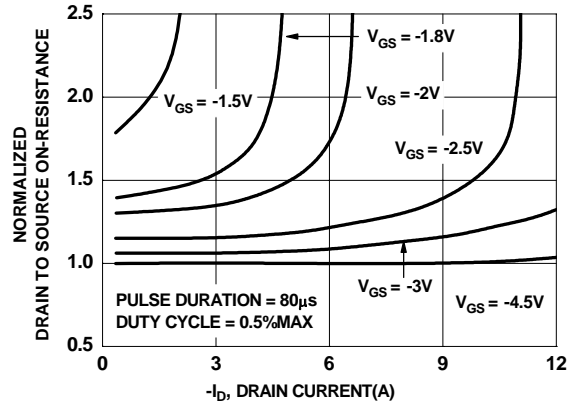


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

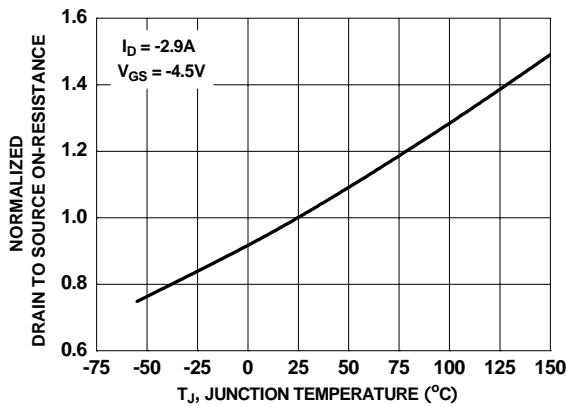


Figure 3. Normalized On-Resistance vs Junction Temperature

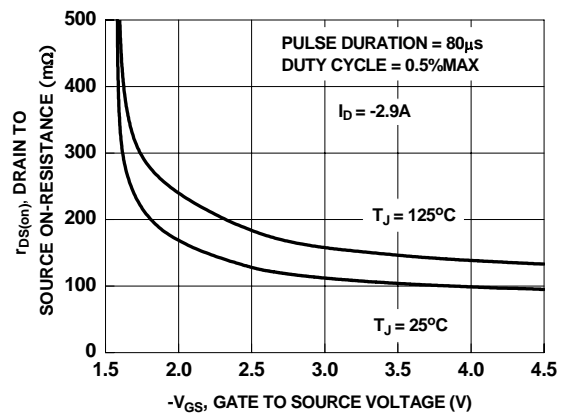


Figure 4. On-Resistance vs Gate to Source Voltage

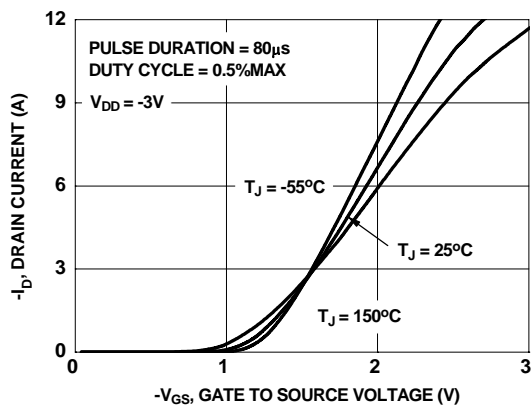


Figure 5. Transfer Characteristics

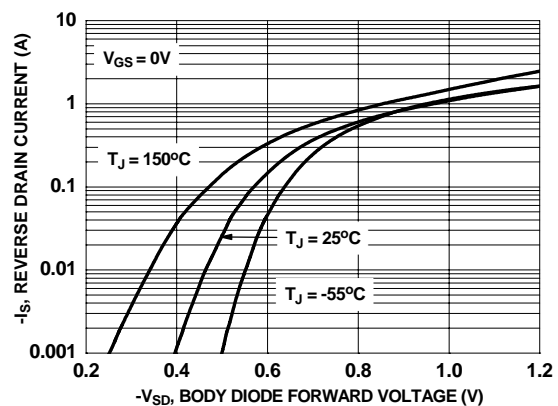


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

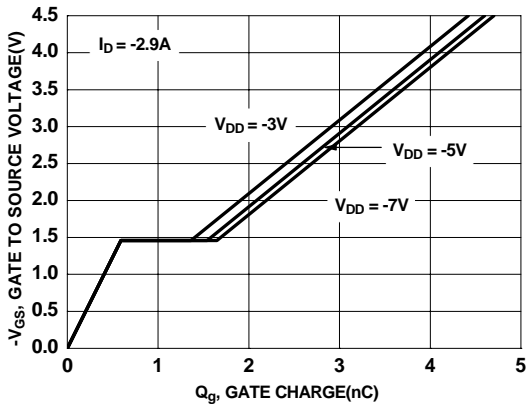


Figure 7. Gate Charge Characteristics

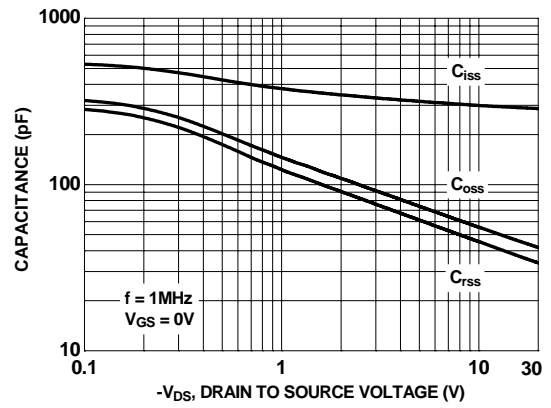


Figure 8. Capacitance vs Drain to Source Voltage

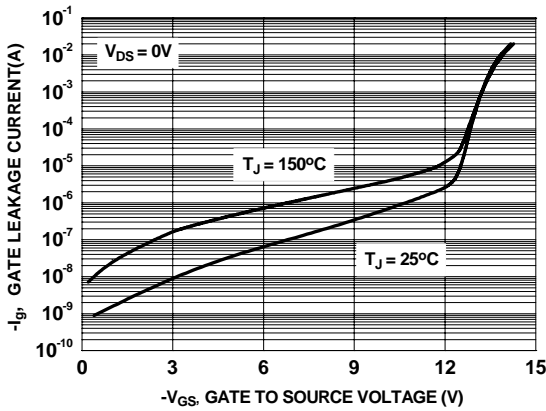


Figure 9. Gate Leakage Current vs Gate to Source Voltage

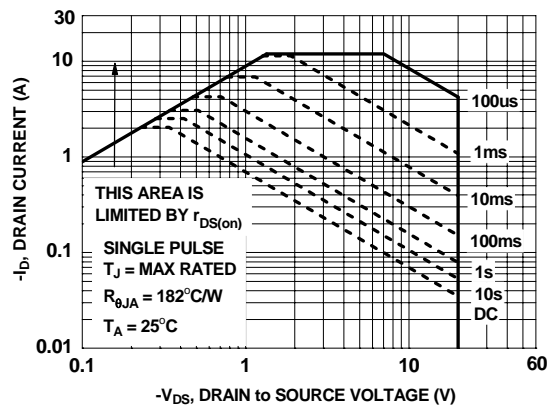


Figure 10. Forward Bias Safe Operating Area

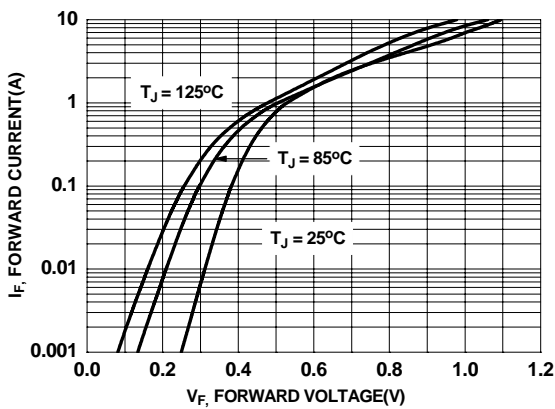


Figure 11. Schottky Diode Forward Voltage

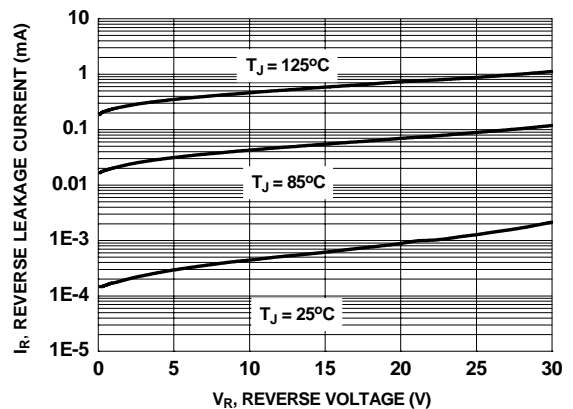


Figure 12. Schottky Diode Reverse Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

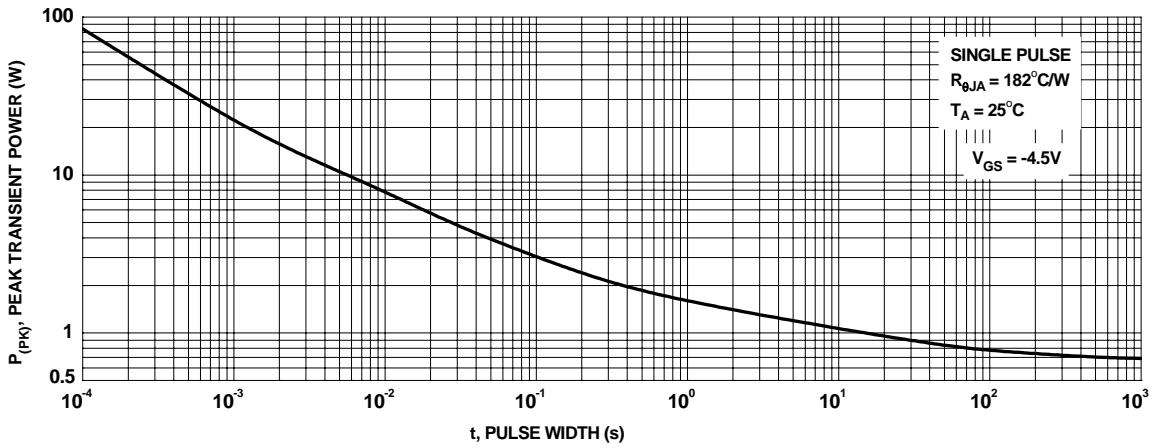


Figure 13. Single Pulse Maximum Power Dissipation

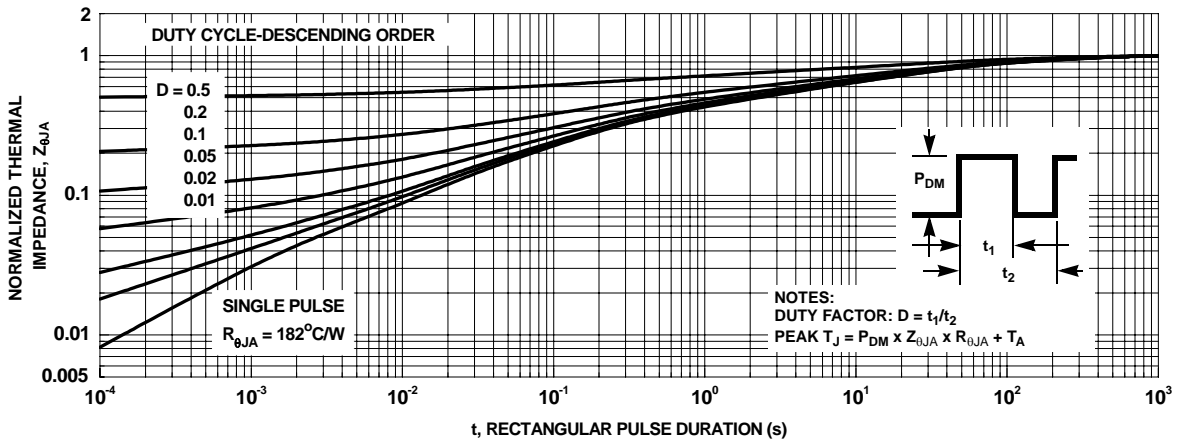
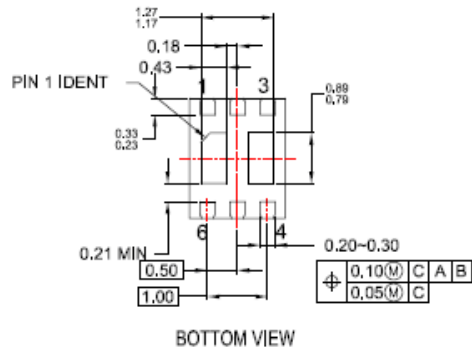
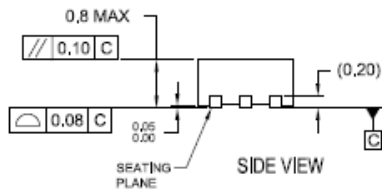
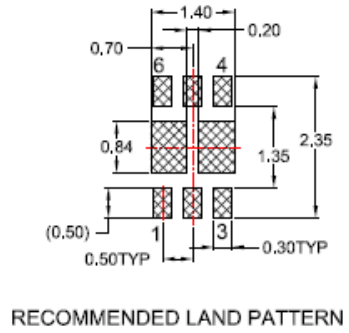
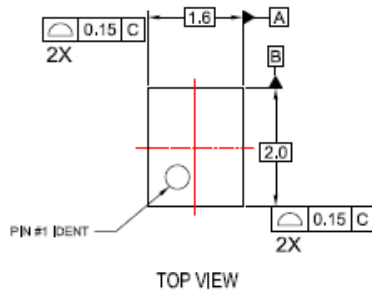


Figure 14. Transient Thermal Response Curve


Dimensional Outline and Pad Layout





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